AN79Lxx/AN79LxxM Series

3-pin negative output voltage regulator (100 mA type)

■ Overview

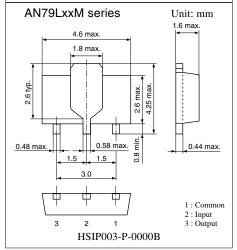
The AN79Lxx series and the AN79LxxM series are 3-pin, fixed negative output type monolithic voltage regulators.

Stabilized fixed output voltage is obtained from unstable DC input voltage without using any external components. 12 types of output voltage are available: -4V, -5V, -6V, -7V, -8V, -9V, -10V, -12V, -15V, -18V, -20V and -24V. They can be used widely in power circuits with current capacity of up to 100mA.

■ Features

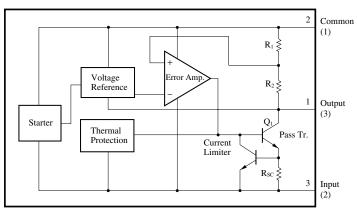
- No external components
- Output voltage: -4V, -5V, -6V, -7V, -8V, -9V, -10V, -12V, -15V, -18V, -20V, -24V
- Built-in overcurrent limit circuit
- Built-in thermal overload protection circuit

AN79Lxx series Unit: mm 4.0±0.2 0.6±0.15 0.43±0.16 0.43±0.16 0.43±0.16 1: Output 2: Common 3: Intput SSIP003-P-0000



Note) The packages (SSIP003-P-0000 and HSIP003-P-0000B) of this product will be changed to lead-free type (SSIP003-P-0000S and HSIP003-P-0000Q). See the new package dimensions section later of this datasheet.

■ Block Diagram (AN79Lxx series)



Note) The number in () shows the pin number for the AN79LxxM series.

■ Absolute Maximum Ratings at T_a = 25°C

Parameter		Symbol	Rating	Unit
Input voltage		V	-35 * ₁	V
		V_{I}	-40 * ²	V
Power dissipation		P_{D}	650 *3	mW
Operating ambient tem	Operating ambient temperature		-20 to +80	°C
Stone on town another	AN79Lxx series		-55 to +150	90
Storage temperature	AN79LxxM series	$T_{ m stg}$	-55 to +125	°C

^{*1} AN79L04, AN79L05/M, AN79L06, AN79L07, AN79L08/M, AN79L09/M, AN79L10, AN79L12/M, AN79L15/M, AN79L18

■ Electrical Characteristics at $T_a = 25$ °C

• AN79L04 (-4V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V_{o}	$T_j = 25^{\circ}C$	-3.84	-4	-4.16	V
Output voltage tolerance	V_{o}	$V_I = -7 \text{ to } -19V, I_O = 1 \text{ to } 70\text{mA}$	-3.8		-4.2	V
Line regulation	REG_{IN}	$V_I = -6 \text{ to } -20 \text{V}, T_j = 25^{\circ}\text{C}$			80	mV
Line regulation	KEOIN	$V_I = -7 \text{ to } -17 \text{V}, T_j = 25^{\circ}\text{C}$		_	40	mV
Load regulation	DEC	$I_0 = 1 \text{ to } 100\text{mA}, T_j = 25^{\circ}\text{C}$		10	60	mV
	REG _L	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$		4.5	30	mV
Bias current	I_{Bias}	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -7 \text{ to } -19 \text{V}, T_j = 25^{\circ}\text{C}$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$			0.1	mA
Output noise voltage	V _{no}	$f = 10$ Hz to 100 kHz, $T_a = 25$ °C		38		μV
Ripple rejection ratio	RR	$V_1 = -7$ to $-17V$, $f = 120Hz$, $T_a = 25$ °C	55	_	_	dB
Minimum input/output voltage difference	V _{DIF(min)}	$T_j = 25^{\circ}C$		0.8	_	V
Output short-circuit current	I _{O(Short)}	$V_I = -35V, T_j = 25^{\circ}C$	_	200	_	mA
Output voltage temperature coefficient	$\Delta V_{O}/T_{a}$	$I_O = 5 \text{mA}$		- 0.4	_	mV/°C

Note 1) The specified condition $T_j = 25^{\circ}C$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

^{*2} AN79L20, AN79L24

^{*3} Follow the derating curve. When T_j exceeds 150°C, the internal circuit cuts off the output.

AN79LxxM series is mounted on a standard board (glass epoxy: 20mm × 20mm × t1.7mm with Cu foil of 1cm² or more).

Note 2) Unless otherwise specified, $V_I = -9V$, $I_O = 40mA$, $C_I = 2\mu F$, $C_O = 1\mu F$, $T_j = 0$ to $125^{\circ}C$

• AN79L05, AN79L05M (-5V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V_{O}	$T_j = 25^{\circ}C$	-4.8	-5	-5.2	V
Output voltage tolerance	V_{O}	$V_I = -8 \text{ to } -20 \text{V}, I_O = 1 \text{ to } 70 \text{mA}$	-4.75	_	-5.25	V
Line regulation	REG_{IN}	$V_I = -7 \text{ to } -21 \text{V}, T_j = 25^{\circ}\text{C}$	—		100	mV
Line regulation	KEOIN	$V_I = -8 \text{ to } -18V, T_j = 25^{\circ}C$	—	_	50	mV
Load regulation	DEC	$I_0 = 1 \text{ to } 100 \text{mA}, T_j = 25^{\circ}\text{C}$		11	60	mV
Load regulation	REG _L	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$		5	30	mV
Bias current	I_{Bias}	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -8 \text{ to } -20 \text{V}, T_j = 25^{\circ}\text{C}$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$			0.1	mA
Output noise voltage	V_{no}	$f = 10$ Hz to 100 kHz, $T_a = 25$ °C		40		μV
Ripple rejection ratio	RR	$V_I = -8 \text{ to } -18V, f = 120Hz, T_a = 25^{\circ}C$	55			dB
Minimum input/output voltage difference	V _{DIF(min)}	$T_j = 25^{\circ}C$		0.8	_	V
Output short-circuit current	$I_{O(Short)}$	$V_I = -35V, T_j = 25^{\circ}C$		200	_	mA
Output voltage temperature coefficient	$\Delta V_{O}/T_{a}$	$I_O = 5mA$	_	- 0.4		mV/°C

Note 1) The specified condition $T_j = 25^{\circ}C$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

• AN79L06 (-6V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V_0	$T_j = 25^{\circ}C$	-5.76	-6	-6.24	V
Output voltage tolerance	V_{0}	$V_I = -9 \text{ to } -21 \text{V}, I_O = 1 \text{ to } 70 \text{mA}$	-5.7		-6.3	V
Line regulation	REG_{IN}	$V_I = -8 \text{ to } -22 \text{V}, T_j = 25^{\circ}\text{C}$			120	mV
Line regulation	KEG _{IN}	$V_I = -9 \text{ to } -19V, T_j = 25^{\circ}C$		_	60	mV
Load regulation	DEC	$I_0 = 1$ to 100mA, $T_j = 25$ °C		12	60	mV
	REG _L	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$		5.5	30	mV
Bias current	I_{Bias}	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -9 \text{ to } -21 \text{V}, T_j = 25^{\circ}\text{C}$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$			0.1	mA
Output noise voltage	V_{no}	$f = 10$ Hz to 100 kHz, $T_a = 25$ °C		44		μV
Ripple rejection ratio	RR	$V_I = -9 \text{ to } -19V, f = 120Hz, T_a = 25^{\circ}C$	55			dB
Minimum input/output voltage difference	$V_{\text{DIF}(\text{min})}$	$T_j = 25^{\circ}C$		0.8	_	V
Output short-circuit current	$I_{O(Short)}$	$V_I = -35V, T_j = 25^{\circ}C$		200	_	mA
Output voltage temperature coefficient	$\Delta V_O/T_a$	$I_O = 5 \text{mA}$		- 0.4	_	mV/°C

Note 1) The specified condition $T_j = 25^{\circ}C$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_1 = -11V$, $I_0 = 40\text{mA}$, $C_1 = 2\mu\text{F}$, $C_0 = 1\mu\text{F}$, $T_1 = 0$ to 125°C

Note 2) Unless otherwise specified, $V_I = -10V$, $I_O = 40 \text{mA}$, $C_I = 2 \mu \text{F}$, $C_O = 1 \mu \text{F}$, $T_j = 0$ to 125°C (AN79L05) and $T_j = 0$ to 100°C (AN79L05M)

• AN79L07 (-7V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	-6.72	-7	-7.28	V
Output voltage tolerance	Vo	$V_I = -10 \text{ to } -22 \text{V}, I_O = 1 \text{ to } 70 \text{mA}$	-6.65		-7.35	V
Line regulation	REGIN	$V_I = -9 \text{ to } -23 \text{V}, T_j = 25^{\circ}\text{C}$			140	mV
Line regulation		$V_I = -10 \text{ to } -20 \text{V}, T_j = 25^{\circ}\text{C}$	_		70	mV
I and manufaction	DEC	$I_0 = 1 \text{ to } 100 \text{mA}, T_j = 25^{\circ}\text{C}$		13	70	mV
Load regulation	REG _L	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$		6	40	mV
Bias current	I_{Bias}	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -10 \text{ to } -22 \text{V}, T_j = 25^{\circ}\text{C}$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$			0.1	mA
Output noise voltage	V_{no}	$f = 10Hz \text{ to } 100kHz, T_a = 25^{\circ}C$		48	_	μV
Ripple rejection ratio	RR	$V_1 = -10 \text{ to } -20 \text{V}, \text{ f} = 120 \text{Hz}, \text{ T}_a = 25^{\circ} \text{C}$	54			dB
Minimum input/output voltage difference	$V_{\text{DIF}(min)}$	$T_j = 25^{\circ}C$		0.8	_	V
Output short-circuit current	I _{O(Short)}	$V_I = -35V, T_j = 25^{\circ}C$		200		mA
Output voltage temperature coefficient	$\Delta V_{O}/T_{a}$	$I_O = 5mA$		- 0.5		mV/°C

Note 1) The specified condition $T_j = 25^{\circ}$ C means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

• AN79L08, AN79L08M (-8V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	-7.68	-8	-8.32	V
Output voltage tolerance	Vo	$V_I = -11 \text{ to } -23 \text{V}, I_O = 1 \text{ to } 70 \text{mA}$	-7.6	_	-8.4	V
Line regulation	REG _{IN}	$V_I = -10 \text{ to } -24 \text{V}, T_j = 25^{\circ}\text{C}$		_	160	mV
Line regulation		$V_I = -11 \text{ to } -21 \text{V}, T_j = 25^{\circ}\text{C}$		_	80	mV
Load regulation	DEC	$I_0 = 1 \text{ to } 100\text{mA}, T_j = 25^{\circ}\text{C}$		15	80	mV
	REG _L	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$		7	40	mV
Bias current	I_{Bias}	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -11 \text{ to } -23 \text{V}, T_j = 25^{\circ}\text{C}$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$			0.1	mA
Output noise voltage	V_{no}	$f = 10$ Hz to 100 kHz, $T_a = 25$ °C	_	52	_	μV
Ripple rejection ratio	RR	$V_I = -11 \text{ to } -21 \text{V}, f = 120 \text{Hz}, T_a = 25^{\circ} \text{C}$	54		_	dB
Minimum input/output voltage difference	$V_{\text{DIF}(\text{min})}$	$T_j = 25^{\circ}C$		0.8	_	V
Output short-circuit current	I _{O(Short)}	$V_I = -35V, T_j = 25^{\circ}C$		200	_	mA
Output voltage temperature coefficient	$\Delta V_O/T_a$	$I_0 = 5 \text{mA}, T_j = 0 \text{ to } 125^{\circ}\text{C}$		- 0.6	_	mV/°C

Note 1) The specified condition $T_j = 25^{\circ}C$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_I = -12V$, $I_O = 40\text{mA}$, $C_I = 2\mu\text{F}$, $C_O = 1\mu\text{F}$, $T_j = 0$ to 125°C

Note 2) Unless otherwise specified, $V_I = -14V$, $I_O = 40mA$, $C_I = 2\mu F$, $C_O = 1\mu F$, $T_j = 0$ to $125^{\circ}C$ (AN79L08) and $T_j = 0$ to $100^{\circ}C$ (AN79L08M)

• AN79L09, AN79L09M (-9V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	-8.64	-9	-9.36	V
Output voltage tolerance	V_{O}	$V_I = -12 \text{ to } -24 \text{V}, I_O = 1 \text{ to } 70 \text{mA}$	-8.55	_	-9.45	V
Line regulation	REG _{IN}	$V_I = -11 \text{ to } -25 \text{V}, T_j = 25^{\circ}\text{C}$		_	160	mV
Line regulation	KEOIN	$V_I = -12 \text{ to } -22V, T_j = 25^{\circ}C$		_	80	mV
Load regulation	DEC	$I_0 = 1 \text{ to } 100\text{mA}, T_j = 25^{\circ}\text{C}$		16	90	mV
	REG _L	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$		8	50	mV
Bias current	I_{Bias}	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -12 \text{ to } -24 \text{V}, T_j = 25^{\circ}\text{C}$	_		0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$		_	0.1	mA
Output noise voltage	V_{no}	$f = 10$ Hz to 100 kHz, $T_a = 25$ °C	_	58	_	μV
Ripple rejection ratio	RR	$V_I = -12 \text{ to } -22 \text{V}, f = 120 \text{Hz}, T_a = 25^{\circ} \text{C}$	53			dB
Minimum input/output voltage difference	V _{DIF(min)}	$T_j = 25^{\circ}C$		0.8	_	V
Output short-circuit current	I _{O(Short)}	$V_I = -35V, T_j = 25^{\circ}C$		200	_	mA
Output voltage temperature coefficient	$\Delta V_{O}/T_{a}$	$I_0 = 5 \text{mA}, T_j = 0 \text{ to } 125^{\circ}\text{C}$		- 0.6		mV/°C

Note 1) The specified condition $T_j = 25^{\circ}C$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

• AN79L10 (-10V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	-9.6	-10	-10.4	V
Output voltage tolerance	V_{o}	$V_I = -13 \text{ to } -25 \text{V}, I_O = 1 \text{ to } 70 \text{mA}$	-9.5		-10.5	V
Line regulation	REG_{IN}	$V_I = -12 \text{ to } -26V, T_j = 25^{\circ}C$			160	mV
Line regulation	KEUIN	$V_I = -13 \text{ to } -23 \text{V}, T_j = 25 ^{\circ}\text{C}$		_	80	mV
Load regulation	DEC	$I_0 = 1 \text{ to } 100\text{mA}, T_j = 25^{\circ}\text{C}$		17	100	mV
	REG _L	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$		9	50	mV
Bias current	I_{Bias}	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -13 \text{ to } -25 \text{V}, T_j = 25 ^{\circ}\text{C}$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$			0.1	mA
Output noise voltage	V_{no}	$f = 10$ Hz to 100 kHz, $T_a = 25$ °C		65	_	μV
Ripple rejection ratio	RR	$V_1 = -13$ to $-23V$, $f = 120Hz$, $T_a = 25$ °C	53		_	dB
Minimum input/output voltage difference	V _{DIF(min)}	$T_j = 25^{\circ}C$		0.8	_	V
Output short-circuit current	I _{O(Short)}	$V_I = -35V, T_j = 25^{\circ}C$		200	_	mA
Output voltage temperature coefficient	$\Delta V_{O}/T_{a}$	$I_0 = 5mA$		- 0.7	_	mV/°C

Note 1) The specified condition $T_j = 25^{\circ}C$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_1 = -16V$, $I_0 = 40\text{mA}$, $C_1 = 2\mu\text{F}$, $C_0 = 1\mu\text{F}$, $T_1 = 0$ to 125°C

Note 2) Unless otherwise specified, $V_I = -15V$, $I_O = 40$ mA, $C_I = 2\mu$ F, $C_O = 1\mu$ F, $T_j = 0$ to 125°C (AN79L09) and $T_j = 0$ to 100°C (AN79L09M)

• AN79L12, AN79L12M (-12V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	-11.5	-12	-12.5	V
Output voltage tolerance	V_{O}	$V_I = -15 \text{ to } -27 \text{V}, I_O = 1 \text{ to } 70 \text{mA}$	-11.4		-12.6	V
Line regulation	REG _{IN}	$V_I = -14.5 \text{ to } -30 \text{V}, T_j = 25^{\circ}\text{C}$			200	mV
Line regulation	KEOIN	$V_I = -15 \text{ to } -25 \text{V}, T_j = 25^{\circ}\text{C}$			100	mV
Load ragulation	DEC	$I_0 = 1 \text{ to } 100 \text{mA}, T_j = 25^{\circ}\text{C}$		20	100	mV
Load regulation	REG _L	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$		10	50	mV
Bias current	I_{Bias}	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -15 \text{ to } -27 \text{V}, T_j = 25^{\circ}\text{C}$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$			0.1	mA
Output noise voltage	V_{no}	$f = 10$ Hz to 100 kHz, $T_a = 25$ °C		75		μV
Ripple rejection ratio	RR	$V_I = -15$ to $-25V$, $f = 120Hz$, $T_a = 25$ °C	52			dB
Minimum input/output voltage difference	V _{DIF(min)}	$T_j = 25^{\circ}C$		0.8	_	V
Output short-circuit current	$I_{O(Short)}$	$V_I = -35V, T_j = 25^{\circ}C$		200	_	mA
Output voltage temperature coefficient	$\Delta V_{O}/T_{a}$	$I_O = 5 \text{mA}$		- 0.8		mV/°C

Note 1) The specified condition $T_j = 25^{\circ}C$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

• AN79L15, AN79L15M (-15V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V_{O}	$T_j = 25^{\circ}C$	-14.4	-15	-15.6	V
Output voltage tolerance	Vo	$V_I = -18 \text{ to } -28 \text{V}, I_O = 1 \text{ to } 70 \text{mA}$	-14.25		-15.75	V
Line regulation	REG _{IN}	$V_I = -17.5 \text{ to } -33 \text{V}, T_j = 25 ^{\circ}\text{C}$			200	mV
Line regulation		$V_I = -18 \text{ to } -28 \text{V}, T_j = 25^{\circ}\text{C}$			100	mV
Load regulation	REG_L	$I_0 = 1 \text{ to } 100\text{mA}, T_j = 25^{\circ}\text{C}$		25	130	mV
		$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$		12	60	mV
Bias current	I_{Bias}	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -18 \text{ to } -30 \text{V}, T_j = 25^{\circ}\text{C}$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$			0.1	mA
Output noise voltage	V_{no}	$f = 10$ Hz to 100 kHz, $T_a = 25$ °C		90		μV
Ripple rejection ratio	RR	$V_1 = -18 \text{ to } -28 \text{V}, \text{ f} = 120 \text{Hz}, \text{ T}_a = 25^{\circ} \text{C}$	51		_	dB
Minimum input/output voltage difference	$V_{\text{DIF}(\text{min})}$	$T_j = 25^{\circ}C$		0.8		V
Output short-circuit current	I _{O(Short)}	$V_I = -35V, T_j = 25^{\circ}C$		200		mA
Output voltage temperature coefficient	$\Delta V_O/T_a$	$I_O = 5mA$		- 0.9		mV/°C

Note 1) The specified condition $T_j = 25^{\circ}C$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_I = -19V$, $I_O = 40 \text{mA}$, $C_I = 2 \mu \text{F}$, $C_O = 1 \mu \text{F}$, $T_j = 0$ to 125°C (AN79L12) and $T_j = 0$ to 100°C (AN79L12M)

Note 2) Unless otherwise specified, $V_I = -23V$, $I_O = 40mA$, $C_I = 2\mu F$, $C_O = 1\mu F$, $T_j = 0$ to 125°C (AN79L15) and $T_j = 0$ to 100°C (AN79L15M)

• AN79L18 (-18V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V_{o}	$T_j = 25^{\circ}C$	-17.3	-18	-18.7	V
Output voltage tolerance	Vo	$V_I = -21 \text{ to } -33 \text{V}, I_O = 1 \text{ to } 70 \text{mA}$	-17.1		-18.9	V
Line regulation	REG _{IN}	$V_I = -21 \text{ to } -33 \text{V}, T_j = 25^{\circ}\text{C}$		_	200	mV
Line regulation	KEOIN	$V_I = -21 \text{ to } -32V, T_j = 25^{\circ}C$			100	mV
Load regulation	DEC	$I_0 = 1 \text{ to } 100\text{mA}, T_j = 25^{\circ}\text{C}$		30	160	mV
Load regulation	REG _L	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$		15	80	mV
Bias current	I_{Bias}	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -21 \text{ to } -33 \text{V}, T_j = 25 ^{\circ}\text{C}$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$			0.1	mA
Output noise voltage	V_{no}	$f = 10$ Hz to 100 kHz, $T_a = 25$ °C		110		μV
Ripple rejection ratio	RR	$V_1 = -22 \text{ to } -32 \text{V}, \text{ f} = 120 \text{Hz}, \text{ T}_a = 25^{\circ} \text{C}$	50		_	dB
Minimum input/output voltage difference	V _{DIF(min)}	$T_j = 25^{\circ}C$		0.8	_	V
Output short-circuit current	I _{O(Short)}	$V_I = -35V, T_j = 25^{\circ}C$		200	_	mA
Output voltage temperature coefficient	$\Delta V_{O}/T_{a}$	$I_0 = 5 \text{mA}$		-1		mV/°C

Note 1) The specified condition $T_j = 25^{\circ}$ C means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

• AN79L20 (-20V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V_{o}	$T_j = 25$ °C	-19.2	-20	-20.8	V
Output voltage tolerance	V_{o}	$V_I = -23 \text{ to } -35 \text{V}, I_O = 1 \text{ to } 70 \text{mA}$	-19		-21	V
Line regulation	REG_{IN}	$V_I = -23 \text{ to } -35 \text{V}, T_j = 25 ^{\circ}\text{C}$			200	mV
Line regulation	KEUIN	$V_I = -24 \text{ to } -34 \text{V}, T_j = 25^{\circ}\text{C}$		_	100	mV
Load regulation	DEC	$I_0 = 1 \text{ to } 100 \text{mA}, T_j = 25^{\circ}\text{C}$		35	180	mV
	REG _L	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$		17	90	mV
Bias current	I_{Bias}	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -23 \text{ to } -35 \text{V}, T_j = 25 ^{\circ}\text{C}$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$			0.1	mA
Output noise voltage	V _{no}	$f = 10Hz \text{ to } 100kHz, T_a = 25^{\circ}C$		135	_	μV
Ripple rejection ratio	RR	$V_I = -24 \text{ to } -34 \text{V}, f = 120 \text{Hz}, T_a = 25^{\circ}\text{C}$	49	_		dB
Minimum input/output voltage difference	V _{DIF(min)}	$T_j = 25$ °C		0.8		V
Output short-circuit current	I _{O(Short)}	$V_I = -35V, T_j = 25^{\circ}C$		200	_	mA
Output voltage temperature coefficient	$\Delta V_{O}/T_{a}$	$I_O = 5mA$		-1		mV/°C

Note 1) The specified condition $T_j = 25^{\circ}C$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_1 = -27V$, $I_0 = 40\text{mA}$, $C_1 = 2\mu\text{F}$, $C_0 = 1\mu\text{F}$, $T_j = 0$ to 125°C

Note 2) Unless otherwise specified, $V_1 = -29V$, $I_0 = 40\text{mA}$, $C_1 = 2\mu\text{F}$, $C_0 = 1\mu\text{F}$, $T_j = 0$ to 125°C

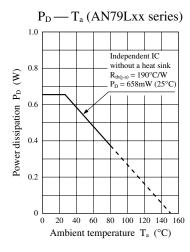
• AN79L24 (-24V type)

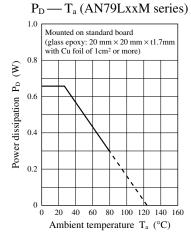
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	-23	-24	-25	V
Output voltage tolerance	V_{o}	$V_I = -27 \text{ to } -38V, I_O = 1 \text{ to } 70\text{mA}$	-22.8		-25.2	V
Line regulation	REG_{IN}	$V_I = -27 \text{ to } -38V, T_j = 25^{\circ}C$			200	mV
		$V_I = -27 \text{ to } -37 \text{V}, T_j = 25^{\circ}\text{C}$			100	mV
Load regulation	REG_L	$I_0 = 1 \text{ to } 100\text{mA}, T_j = 25^{\circ}\text{C}$		40	200	mV
		$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$		20	100	mV
Bias current	I_{Bias}	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -27 \text{ to } -38 \text{V}, T_j = 25 ^{\circ}\text{C}$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$			0.1	mA
Output noise voltage	V_{no}	$f = 10$ Hz to 100 kHz, $T_a = 25$ °C		170		μV
Ripple rejection ratio	RR	$V_1 = -28 \text{ to } -38 \text{V}, \text{ f} = 120 \text{Hz}, \text{ T}_a = 25^{\circ} \text{C}$	49		_	dB
Minimum input/output voltage difference	V _{DIF(min)}	$T_j = 25^{\circ}C$		0.8		V
Output short-circuit current	I _{O(Short)}	$V_I = -35V, T_j = 25^{\circ}C$		200		mA
Output voltage temperature coefficient	$\Delta V_O/T_a$	$I_{O} = 5 \text{mA}$		-1		mV/°C

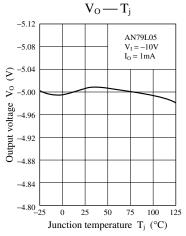
Note 1) The specified condition $T_j = 25^{\circ}$ C means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_1 = -33V$, $I_0 = 40mA$, $C_1 = 2\mu F$, $C_0 = 1\mu F$, $T_1 = 0$ to $125^{\circ}C$

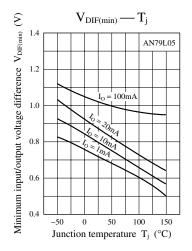
■ Main Characteristics

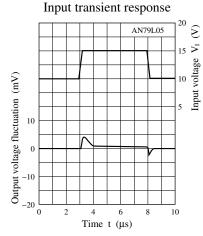


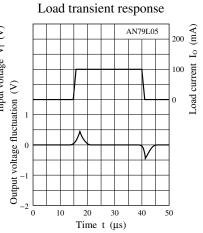


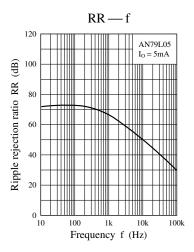


■ Main Characteristics (continued)

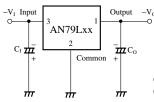








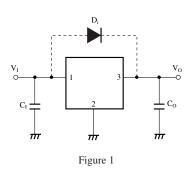
■ Basic Regulator Circuit



Connect C_I of $2\mu F$ when the input line is long. C_O improves the transient response. $1\mu F$

■ Usage Notes

1. Cautions for a basic circuit



- C_{I} : When a wiring from a smoothing circuit to a three-pin regulator is long, it is likely to oscillate at output. A capacitor of $0.1\mu F$ to $0.47\mu F$ should be connected near an input pin.
- C_{O} : Deadly needed to prevent from oscillation (0.33 μ F to 1.0 μ F). It is recommended to use a capacitor of a small internal impedance (ex. tantalum capacitor) when using it under a low temperature.

When any sudden change of load current is likely to occur, connect an electrolytic capacitor of $10\mu F$ to $100\mu F$ to improve a transitional response of output voltage.

D_i: Normally unnecessary. But add it in the case that there is a residual voltage at the output capacitor Co even after switching off the supply power because a current is likely to flow into an output pin of the IC and damage the IC.

2. Other caution items

1) Short-circuit between the input pin and GND pin

If the input pin is short-circuitted to GND or is cut off when a large capacitance capacitor has been connected to the IC's load, a voltage of a capacitor connected to an output pin is applied between input/output of the IC and this likely results in damage of the IC. It is necessary, therefore, to connect a diode, as shown in figure 2, to counter the reverse bias between input/output pins.

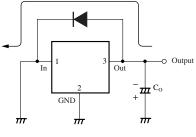
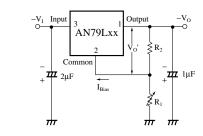


Figure 2

2) Floating of GND pin

If a GND pin is made floating in an operating mode, an unstabilized input voltage is outputted. In this case, a thermal protection circuit inside the IC does not normally operate. In this state, if the load is short-circuited or overloaded, it is likely to damage the IC.

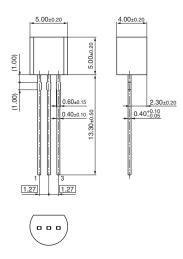
■ Application Circuit Example



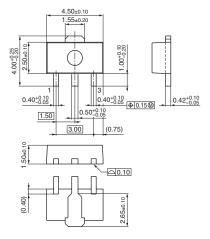
$$\left|V_{O}\right| = V_{O}'\left(1 + \frac{R_{1}}{R_{2}}\right) + I_{Q}R_{1}$$

Note) V_0 varies due to sample to sample variation of $I_{\mbox{\tiny Bias}}$. Never fail to adjust individually with R_1 .

- New Package Dimensions (Unit: mm)
- SSIP003-P-0000S (Lead-free package)



• HSIP003-P-0000Q (Lead-free package)



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